D6-7-785-70-P

Application

Laser Projector

Measuring equipment

Property

Wavelength λ = 785 nm

Output Power = 70 mW

Package Type = φ 5.6mm

Introduction

Egismos currently markets AlGaAs infrared laser diodes in the 780nm ~ 1550nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer. Egismos laser diodes are highly rated in a broad range of applications including, but not limited to, laser pointers,

Laser Diode Key features

Absolute Maximum Rating at Tc=25℃

Items	Symbols	Values	Unit
Operating Current power	P_o	70	mW
Reverse Voltage	V_R	2	V
Operating Temperature	T_{case}	-10~+70	℃
Storage Temperature	T_s	-40~+80	℃

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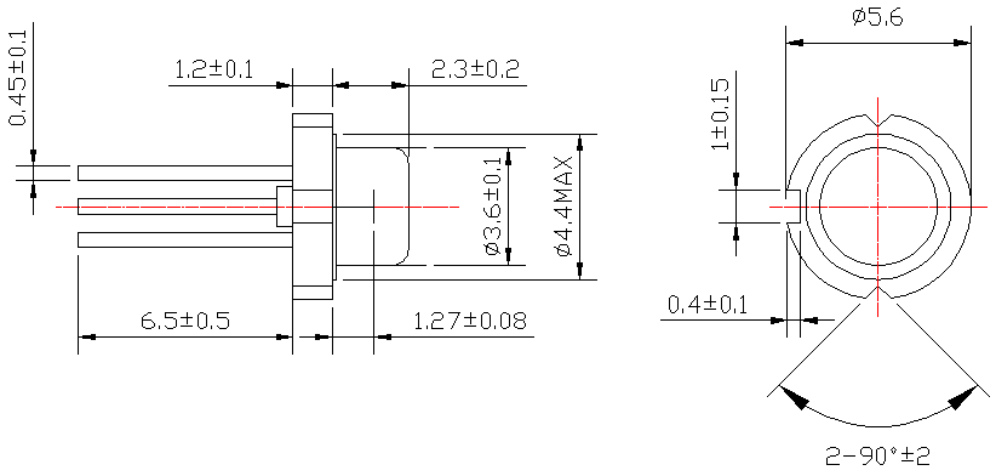
785nm RED Laser Diode

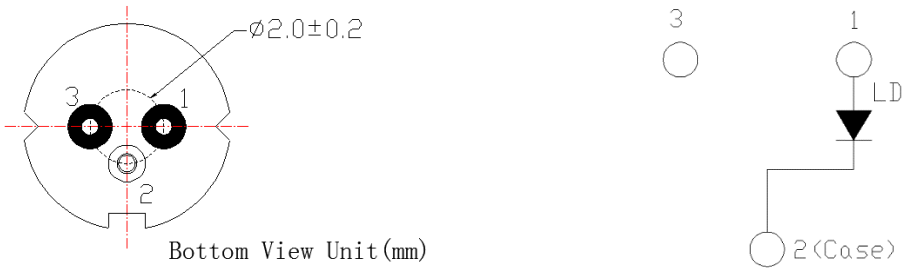
Electrical and Optical Characteristics at Tc=25℃

Item	Symbols	Min	Typ.	Max.	Unit	Condition
Threshold Current	I_{th}	-	40	60	mA	-
Operating Current	I_{op}	80	110	140	mA	Po=70mW
Operating Voltage	V_{op}	-	1.8	2.3	V	Po=70mW
Peak Wavelength	λ p	770	785	795	nm	Po=70mW
Beam Divergence (FWHM)	$\theta_{//}$	7.5	8.5	9.5	deg	Po=70mW
Beam Divergence (FWHM)	$\theta_{\perp}$	14	16	18	deg	Po=70mW

Package Drawing



ELECTRICAL CONNECTION



Specifications are subject to change without notice.

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